

MOS FIELD EFFECT TRANSISTOR

μ PA502T

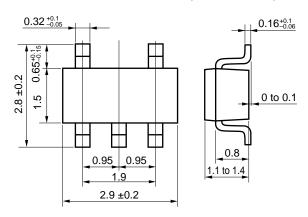
N-CHANNEL MOS FET (5-PIN 2 CIRCUITS)

The μ PA502T is a mini-mold device provided with two MOS FET circuits. It achieves high-density mounting and saves mounting costs.

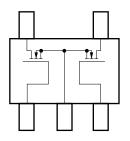
FEATURES

- Two source common MOS FET circuits in package the same size as SC-59
- Complement to μPA503T
- · Automatic mounting supported

PACKAGE DIMENSIONS (in millimeters)



PIN CONNECTION (Top view)



ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain to Source Voltage	VDSS	50	V	
Gate to Source Voltage	Vgss	±20	V	
Drain Current (DC)	I _{D(DC)}	100	mA	
Drain Current (pulse)	I _{D(pulse)} *	200	mA	
Total Power Dissipation	Рт	300 (TOTAL)	mW	
Channel Temperature	Tch	150	°C	
Storage Temperature	Tstg	-55 to 150	°C	

^{*} PW \leq 10 ms, Duty Cycle \leq 50 %

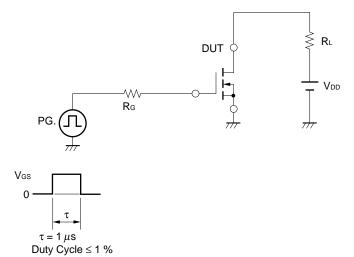


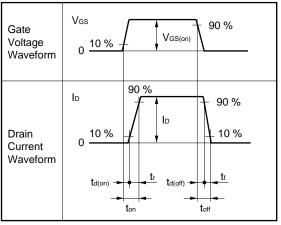
ELECTRICAL CHARACTERISTICS (TA = 25 °C)

PARAMETER	SYMBOL	TEST CONDITIONS N		TYP.	MAX.	UNIT
Drain Cut-off Current	IDSS	V _{DS} = 50 V, V _{GS} = 0			1.0	μΑ
Gate Leakage Current	Igss	Vgs = ±20 V, Vps = 0			±1.0	μΑ
Gate Cut-off Voltage	V _{GS(off)}	$V_{DS} = 5.0 \text{ V}, I_{D} = 1.0 \mu A$	0.8	1.4	1.8	V
Forward Transfer Admittance	yfs	V _{DS} = 5.0 V, I _D = 10 mA	20			mS
Drain to Source On-State Resistance	RDS(on)1	Vgs = 4.0 V, ID = 10 mA		19	30	Ω
Drain to Source On-State Resistance	RDS(on)2	Vgs = 10 V, Ip = 10 mA		15	25	Ω
Input Capacitance	Ciss	V _{DS} = 5.0 V, V _{GS} = 0, f = 1.0 MHz		16		pF
Output Capacitance	Coss			12		PF
Reverse Transfer Capacitance	Crss			3		pF
Turn-On Delay Time		$t_{d(on)} V_{GS(on)} = 5.0 \text{ V}, \text{ Rg} = 10 \Omega$		17		ns
Rise Time	tr	V _{DD} = 5.0 V, I _D = 10 mA		10		ns
Turn-Off Delay Time	td(off)	$R_L = 500 \Omega$		68		ns
Fall Time	tf			38		ns

Marking: DA

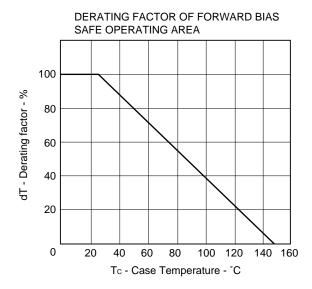
SWITCHING TIME MEASUREMENT CIRCUIT AND MEASUREMENT CONDITIONS (RESISTANCE LOADED)

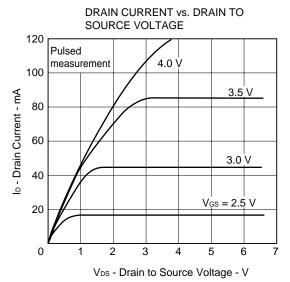


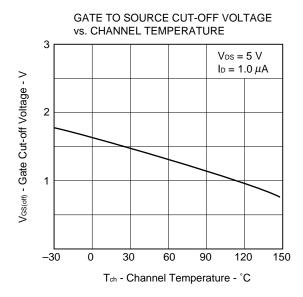


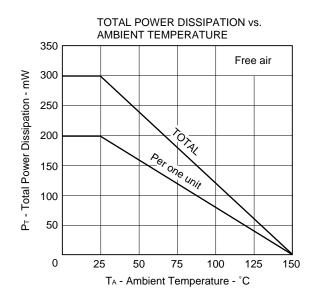


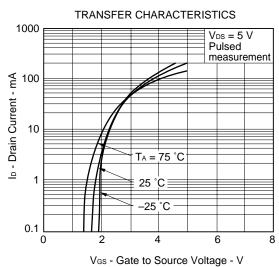
TYPICAL CHARACTERISTICS (TA = 25 °C)

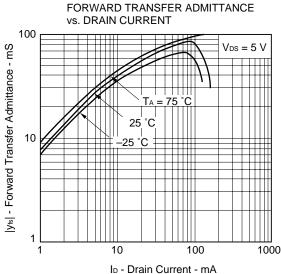








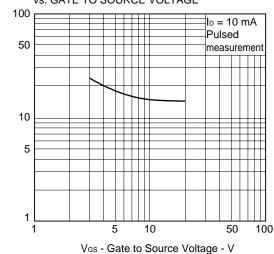




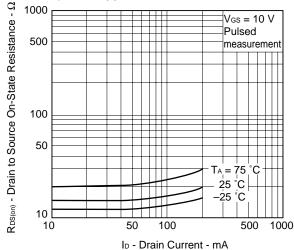


 $\mathsf{R}^{\mbox{\tiny DS}(\mbox{\tiny On})}$ - Drain to Source On-State Resistance - Ω

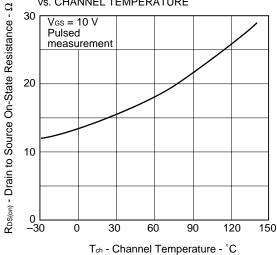
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



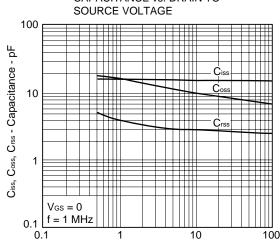
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE

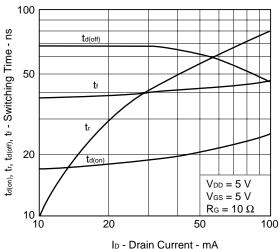


CAPACITANCE vs. DRAIN TO

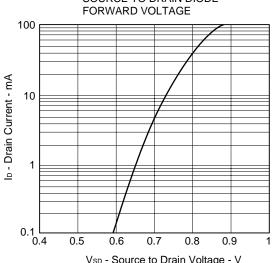


V_{DS} - Drain to Source Voltage - V

SWITCHING CHARACTERISTICS



SOURCE TO DRAIN DIODE



VsD - Source to Drain Voltage - V



REFERENCE

Document Name	Document No.	
NEC semiconductor device reliability/quality control system	TEI-1202	
Quality grade on NEC semiconductor devices	IEI-1209	
Semiconductor device mounting technology manual	C10535E	
Guide to quality assurance for semiconductor devices	MEI-1202	
Semiconductor selection guide	X10679E	



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Anti-radioactive design is not implemented in this product.

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